

Silicon NPN Power Transistors

2N6495

DESCRIPTION

- With TO-66 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- Designed for switching and wide-band amplifier applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

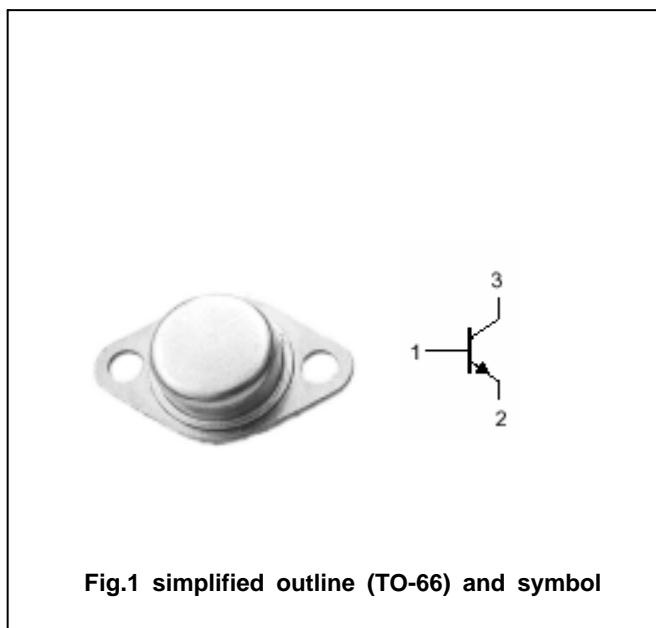


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		10	A
P _T	Total power dissipation	T _C =25	70	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	4.37	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A ; I _B =0	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A; I _B =1A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A; I _B =1A			2.0	V
V _{BE}	Base -emitter on voltage	I _C =10A ; V _{CE} =3V			2.8	V
I _{CEV}	Collector cut-off current	V _{CE} =150V; V _{BE(off)} =-1.5V T _C =150			0.1 1.0	mA
I _{CEO}	Collector cut-off current	V _{CE} =40V; I _B =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =10A ; V _{CE} =3V	10		60	
f _T	Transition frequency	I _C =1 A ; V _{CE} =10V		25		MHz

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PACKAGE OUTLINE

